优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

- BV_{CEO} > -100V
- I_C = -3A Continuous Collector Current
- I_{CM} = -8A Peak Pulse Current
- $R_{CE(sat)}$ = 110mΩ (Typ)
- Rated to +175°C – Ideal for High Ambient Temperature Environments
- Complementary Part: DXTN3C100PDQ
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

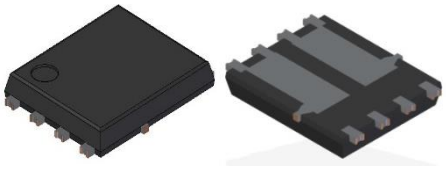
Mechanical Data

- Package: PowerDI5060-8/SWP (Type UXD)
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Lead-Frame; Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.097 grams (Approximate)

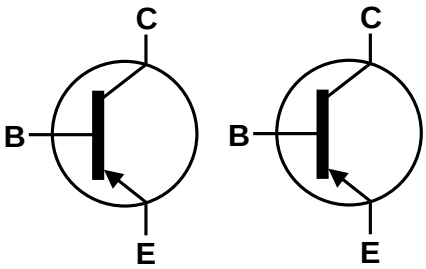
Applications

- Power Management
- Load Switches

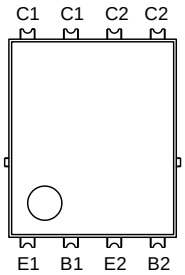
PowerDI5060-8/SWP (Type UXD)



Top View Bottom View



Internal Schematic



Top View
Pin Configuration

Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-7	V
Base Current	I_B	-0.5	A
Continuous Collector Current	I_C	-3	A
Peak Pulse Collector Current	I_{CM}	-8	A

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

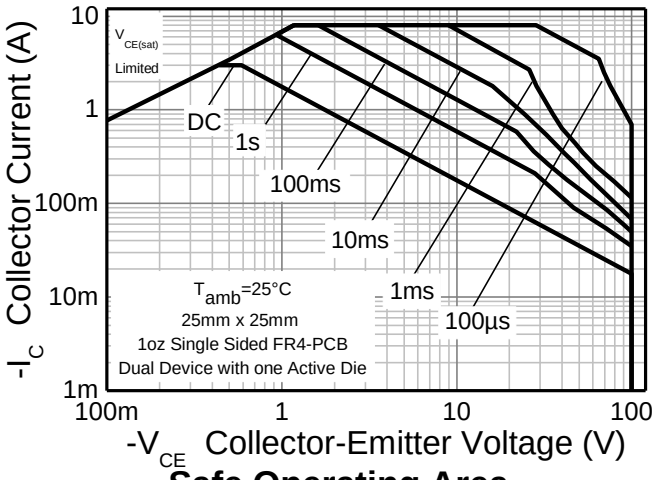
Characteristic		Symbol	Value	Unit
Power Dissipation	(Notes 5 & 7)	P_D	1.76	W
Linear Derating Factor	(Notes 6 & 7)		11.7	mW/°C
Thermal Resistance, Junction to Ambient	(Notes 5 & 7)	$R_{\theta JA}$	85	°C/W
	(Notes 6 & 7)		37	
Thermal Resistance, Junction to Lead	(Note 8)	$R_{\theta JL}$	5.7	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

ESD Ratings (Note 9)

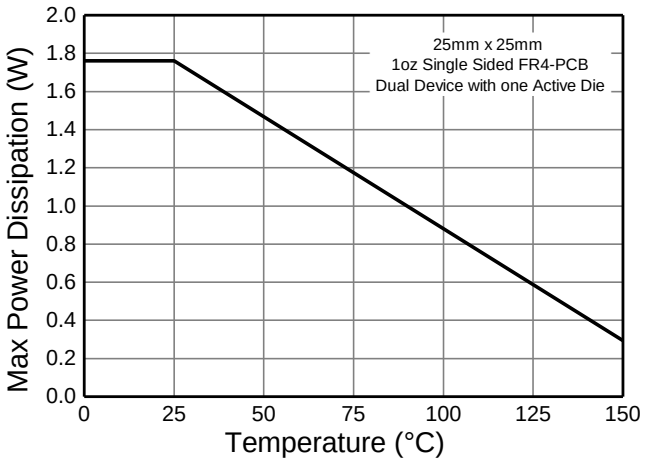
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge – Charged Device Model	ESD CDM	1000	V	C3

Notes:
5. For a device mounted with the collector lead on 25mm x 25mm 1oz copper that is on single-sided 1.6mm FR4 PCB; device with one active die is measured under still air conditions whilst operating in a steady-state.
6. Same as Note 5, except the device is measured at t ≤ 5 sec.
7. For a dual device with one active die.
8. Thermal resistance from junction to solder-point (at the end of the collector lead).
9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

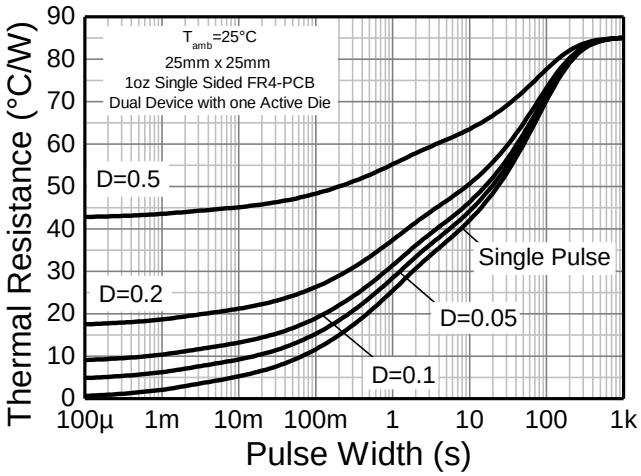
Thermal Characteristics and Derating Information



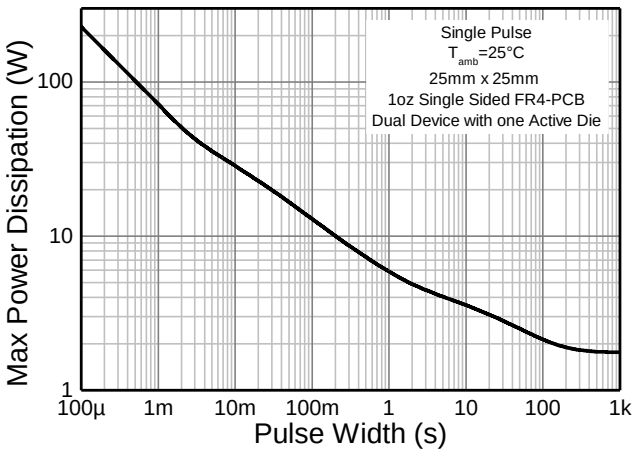
Safe Operating Area



Derating Curve



Transient Thermal Impedance



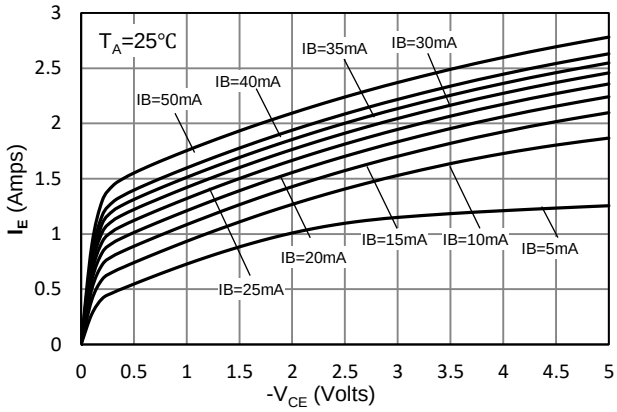
Pulse Power Dissipation

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

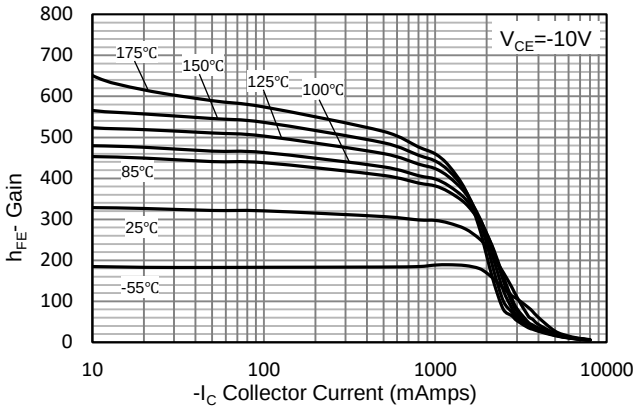
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	-100	—	—	V	I_C = -100μA
Collector-Emitter Breakdown Voltage (Note10)	BV_{CEO}	-100	—	—	V	I_C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	—	—	V	I_E = -100μA
Collector-Base Cutoff Current	I_{CBO}	—	—	-100	nA	V_{CB} = -80V
		—	—	-50	μA	V_{CB} = -80V @Tj = 150°C
Emitter Cutoff Current	I_{EBO}	—	—	-100	nA	V_{EB} = -7V
Collector-Emitter Cutoff Current	I_{CES}	—	—	-100	nA	V_{CES} = -80V
ON CHARACTERISTICS (Note10)						
DC Current Gain	h_{FE}	170	305	—	—	I_C = -500mA, V_{CE} = -10V
		160	275	—		I_C = -1A, V_{CE} = -10V
		45	90	—		I_C = -2A, V_{CE} = -10V
		10	20	—		I_C = -3A, V_{CE} = -10V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	-70	-110	mV	I_C = -0.5A, I_B = -50mA
		—	-220	-325		I_C = -2A, I_B = -200mA
Collector-Emitter Saturation Resistance	$R_{CE(sat)}$	—	110	180	mΩ	I_C = -2A, I_B = -200mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	-0.91	-1	V	I_C = -1A, I_B = -50mA
		—	-1.02	-1.2		I_C = -2A, I_B = -200mA
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	—	-0.68	-0.9	V	I_C = -0.1A, V_{CE} = -2V
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f_T	—	100	—	MHz	V_{CE} = -10V, I_C = -100mA, f = 100MHz
Output Capacitance	C_{obo}	—	30	—	pF	V_{CB} = -10V, f = -1MHz
Delay Time	t_d	—	30	—	ns	V_{CC} = -12.5V, I_C = -1A I_{B1} = -I_{B2} = -50mA
Rise Time	t_r	—	30	—	ns	
Turn-On Time	t_{on}	—	60	—	ns	
Storage Time	t_s	—	660	—	ns	
Fall Time	t_f	—	50	—	ns	
Turn-Off Time	t_{off}	—	710	—	ns	

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

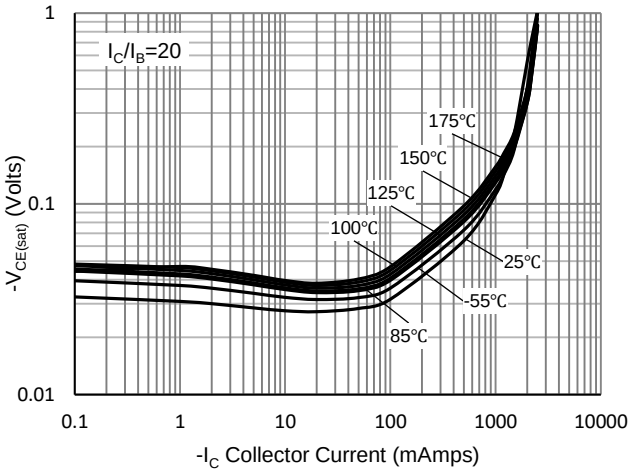
Typical Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)



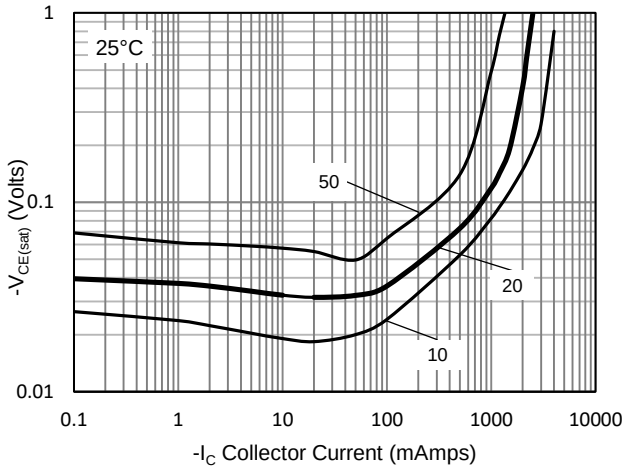
V_{CE} vs I_E



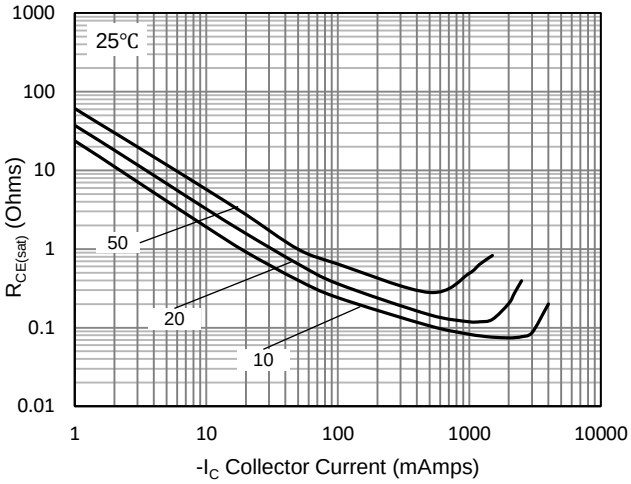
h_{FE} vs I_C



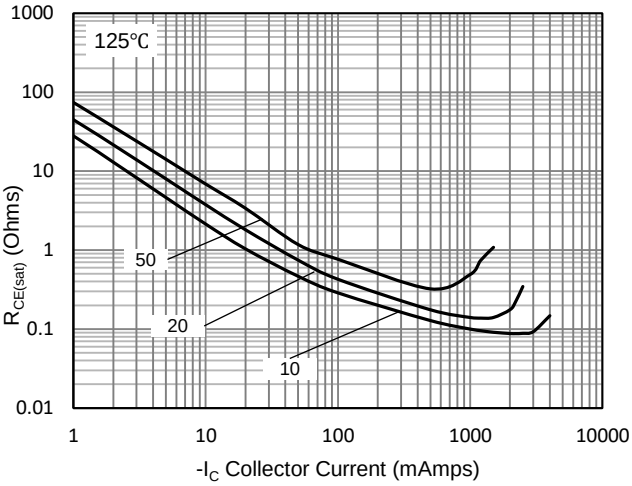
$V_{CE(sat)}$ vs I_C



$V_{CE(sat)}$ vs I_C

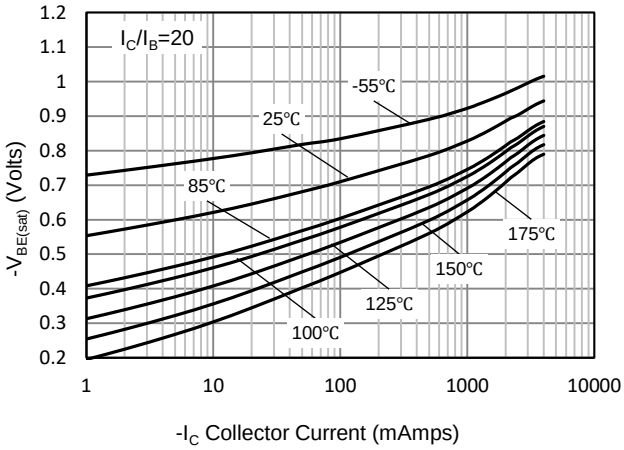


$R_{CE(sat)}$ vs I_C

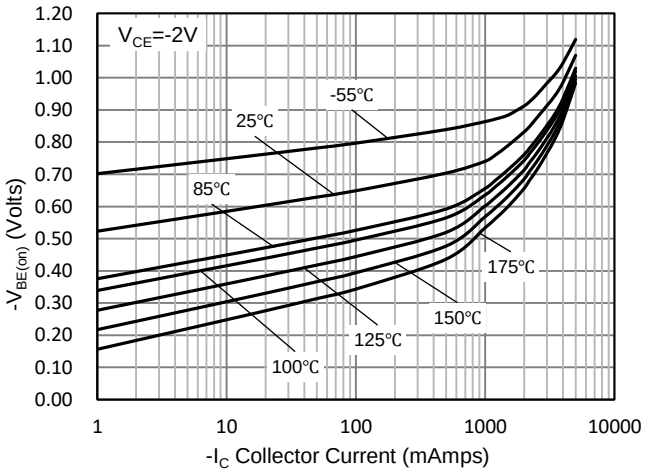


$R_{CE(sat)}$ vs I_C

Typical Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)



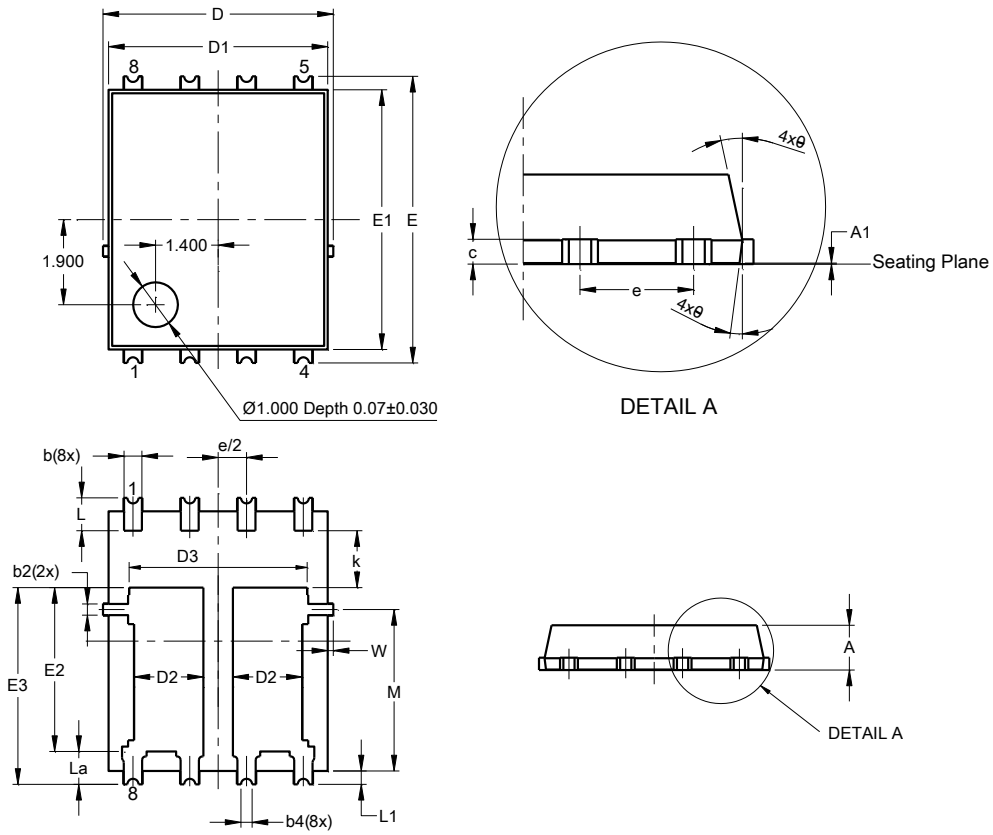
$V_{BE(sat)}$ vs I_C



$V_{BE(on)}$ vs I_C

Package Outline Dimensions

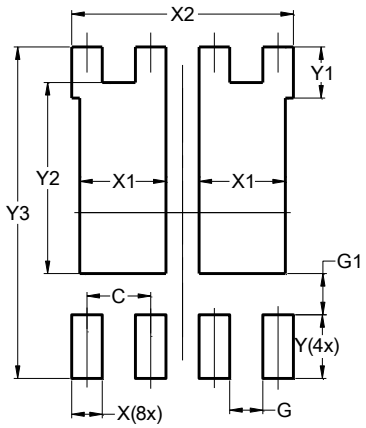
PowerDI5060-8/SWP (Type UXD)



PowerDI5060-8/SWP (Type UXD)			
Dim	**Min**	**Max**	**Typ**
A	0.90	1.10	1.00
A1	0.00	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	1.46	1.66	1.55
D3	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
M	3.205	4.005	3.605
W	0.025	0.225	0.125
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

PowerDI5060-8/SWP (Type UXD)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	1.720
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610